



AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently amended) A semiconductor device comprising a III-V Nitride semiconductor epitaxial film having 4H-polytype structure formed in contact with a substrate having 4H-type structure, wherein 4H-AlN is formed in contact with the substrate.
2. (Original) The semiconductor device according to claim 1, wherein the substrate is silicon carbide.
3. (Previously presented) The semiconductor device according to claim 1, wherein said III-V Nitride semiconductor epitaxial film is formed in contact with a substrate having (11-20) face.
4. (Cancelled)
5. (Previously presented) The semiconductor device according to claim 1, wherein a number of group III atoms are equal to a number of nitrogen atoms on a surface of said III-V Nitride semiconductor epitaxial film.
- 6-50. (Cancelled)